# SiA813DJ

Vishay Siliconix

## P-Channel 20-V (D-S) MOSFET with Schottky Diode

| PRODUCT SUMMARY | | | |
|---|---|---|---|
| $V_{DS}$ (V) | $R_{DS(on)}$ (Ω) | $I_D$ (A)[a] | $Q_g$ |
| - 20 | 0.094 at $V_{GS}$ = - 4.5 V | - 4.5 | 4.9 nC |
| | 0.131 at $V_{GS}$ = - 2.5 V | - 4.5 | |
| | 0.185 at $V_{GS}$ = - 1.8 V | - 4.5 | |

| SCHOTTKY PRODUCT SUMMARY | | |
|---|---|---|
| $V_{KA}$ (V) | $V_f$ (V) Diode Forward Voltage | $I_F$ (A)[a] |
| 20 | 0.46 at 0.5 A | 1 |

### FEATURES

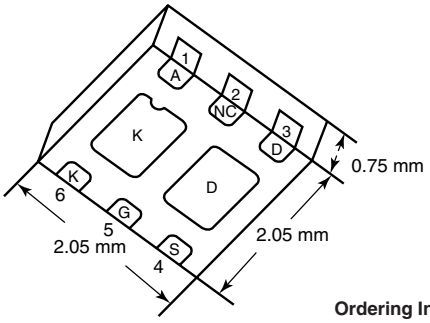
- **Halogen-free According to IEC 61249-2-21 Definition**
- LITTLE FOOT® *Plus* Schottky Power MOSFET
- New Thermally Enhanced PowerPAK® SC-70 Package
  - Small Footprint Area
  - Low On-Resistance
  - Thin 0.75 mm Profile
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE

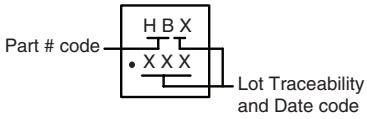
### APPLICATIONS

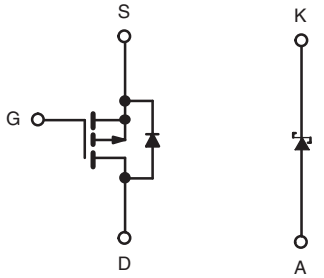
- Cellular Charger Switch
- Buck Converter for Portable Devices
- Load Switch for Portable Devices

**PowerPAK SC-70-6 Dual**




**Marking Code**




P-Channel MOSFET

**Ordering Information:** SiA813DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

| ABSOLUTE MAXIMUM RATINGS $T_A$ = 25 °C, unless otherwise noted | | | | |
|---|---|---|---|---|
| **Parameter** | | **Symbol** | **Limit** | **Unit** |
| Drain-Source Voltage (MOSFET) | | $V_{DS}$ | - 20 | V |
| Reverse Voltage (Schottky) | | $V_{KA}$ | 20 | |
| Gate-Source Voltage (MOSFET) | | $V_{GS}$ | ± 8 | |
| Continuous Drain Current ($T_J$ = 150 °C) (MOSFET) | $T_C$ = 25 °C | $I_D$ | - 4.5[a] | A |
| | $T_C$ = 70 °C | | - 4.5[a] | |
| | $T_A$ = 25 °C | | - 3.6[b, c] | |
| | $T_A$ = 70 °C | | - 2.9[b, c] | |
| Pulsed Drain Current (MOSFET) | | $I_{DM}$ | - 8 | |
| Continuous Source-Drain Diode Current (MOSFET Diode Conduction) | $T_C$ = 25 °C | $I_S$ | - 4.5[a] | |
| | $T_A$ = 25 °C | | - 1.6[b, c] | |
| Average Forward Current (Schottky) | | $I_F$ | 1[b] | |
| Pulsed Forward Current (Schottky) | | $I_{FM}$ | 2 | |
| Maximum Power Dissipation (MOSFET) | $T_C$ = 25 °C | $P_D$ | 6.5 | W |
| | $T_C$ = 70 °C | | 5 | |
| | $T_A$ = 25 °C | | 1.9[b, c] | |
| | $T_A$ = 70 °C | | 1.2[b, c] | |
| Maximum Power Dissipation (Schottky) | $T_C$ = 25 °C | | 7.3 | |
| | $T_C$ = 70 °C | | 4.7 | |
| | $T_A$ = 25 °C | | 2.3[b, c] | |
| | $T_A$ = 70 °C | | 1.5[b, c] | |
| Operating Junction and Storage Temperature Range | | $T_J$, $T_{stg}$ | - 55 to 150 | °C |
| Soldering Recommendations (Peak Temperature)[d, e] | | | 260 | |

## THERMAL RESISTANCE RATINGS

| Parameter | | Symbol | Typical | Maximum | Unit |
|---|---|---|---|---|---|
| Maximum Junction-to-Ambient (MOSFET)[b, f] | t ≤ 5 s | $R_{thJA}$ | 52 | 65 | °C/W |
| Maximum Junction-to-Case (Drain) (MOSFET) | Steady State | $R_{thJC}$ | 12.5 | 16 | |
| Maximum Junction-to-Ambient (Schottky)[b, g] | t ≤ 5 s | $R_{thJA}$ | 40 | 55 | |
| Maximum Junction-to-Case (Drain) (Schottky) | Steady State | $R_{thJC}$ | 13 | 17 | |

Notes:
a. Package limited.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 5 s.
d. See solder profile (www.vishay.com/ppg?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
f. Maximum under steady state conditions for MOSFET is 110 °C/W.
g. Maximum under steady state conditions for Schottky is 85 °C.

## SPECIFICATIONS $T_J$ = 25 °C, unless otherwise noted

| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|
| **Static** | | | | | | |
| Drain-Source Breakdown Voltage | $V_{DS}$ | $V_{GS}$ = 0 V, $I_D$ = - 250 µA | - 20 | | | V |
| $V_{DS}$ Temperature Coefficient | $\Delta V_{DS}/T_J$ | $I_D$ = - 250 µA | | - 16.2 | | mV/°C |
| $V_{GS(th)}$ Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | | | 2.1 | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = - 250 µA | - 0.4 | | - 1 | V |
| Gate-Source Leakage | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ± 8 V | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = - 20 V, $V_{GS}$ = 0 V | | | - 1 | µA |
| | | $V_{DS}$ = - 20 V, $V_{GS}$ = 0 V, $T_J$ = 55 °C | | | - 10 | |
| On-State Drain Current[a] | $I_{D(on)}$ | $V_{DS} \leq$ 5 V, $V_{GS}$ = - 4.5 V | - 8 | | | A |
| Drain-Source On-State Resistance[a] | $R_{DS(on)}$ | $V_{GS}$ = - 4.5 V, $I_D$ = - 2.8 A | | 0.078 | 0.094 | Ω |
| | | $V_{GS}$ = - 2.5 V, $I_D$ = - 2.3 A | | 0.109 | 0.131 | |
| | | $V_{GS}$ = - 1.8 V, $I_D$ = - 0.54 A | | 0.153 | 0.185 | |
| Forward Transconductance[a] | $g_{fs}$ | $V_{DS}$ = - 10 V, $I_D$ = - 2.8 A | | 7 | | S |
| **Dynamic[b]** | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{DS}$ = - 10 V, $V_{GS}$ = 0 V, f = 1 MHz | | 355 | | pF |
| Output Capacitance | $C_{oss}$ | | | 75 | | |
| Reverse Transfer Capacitance | $C_{rss}$ | | | 50 | | |
| Total Gate Charge | $Q_g$ | $V_{DS}$ = - 10 V, $V_{GS}$ = - 8 V, $I_D$ = - 4.5 A | | 8.5 | 13 | nC |
| | | $V_{DS}$ = - 10 V, $V_{GS}$ = - 4.5 V, $I_D$ = - 4.5 A | | 4.9 | 7.4 | |
| Gate-Source Charge | $Q_{gs}$ | | | 0.75 | | |
| Gate-Drain Charge | $Q_{gd}$ | | | 1.2 | | |
| Gate Resistance | $R_g$ | f = 1 MHz | | 8 | | Ω |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD}$ = - 10 V, $R_L$ = 2.2 Ω<br>$I_D \cong$ - 4.5 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 1 Ω | | 10 | 15 | ns |
| Rise Time | $t_r$ | | | 35 | 55 | |
| Turn-Off DelayTime | $t_{d(off)}$ | | | 40 | 60 | |
| Fall Time | $t_f$ | | | 50 | 75 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD}$ = - 10 V, $R_L$ = 2.2 Ω<br>$I_D \cong$ - 4.5 A, $V_{GEN}$ = - 8 V, $R_g$ = 1 Ω | | 5 | 10 | |
| Rise Time | $t_r$ | | | 10 | 15 | |
| Turn-Off DelayTime | $t_{d(off)}$ | | | 20 | 30 | |
| Fall Time | $t_f$ | | | 10 | 15 | |

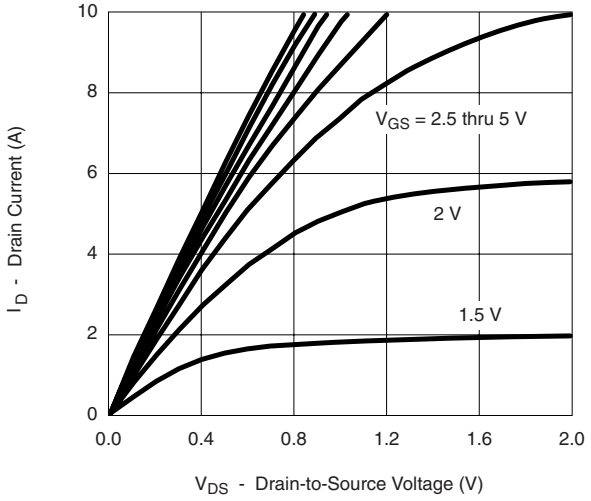
| **SPECIFICATIONS** $T_J$ = 25 °C, unless otherwise noted | | | | | | |
|---|---|---|---|---|---|---|
| **Parameter** | **Symbol** | **Test Conditions** | **Min.** | **Typ.** | **Max.** | **Unit** |
| **Drain-Source Body Diode Characteristics** | | | | | | |
| Continuous Source-Drain Diode Current | $I_S$ | $T_C$ = 25 °C | | | - 4.5 | A |
| Pulse Diode Forward Current | $I_{SM}$ | | | | - 8 | |
| Body Diode Voltage | $V_{SD}$ | $I_S$ = - 4.5 A, $V_{GS}$ = 0 V | | - 0.85 | - 1.2 | V |
| Body Diode Reverse Recovery Time | $t_{rr}$ | $I_F$ = - 4.5 A, dI/dt = 100 A/µs, $T_J$ = 25 °C | | 30 | 60 | ns |
| Body Diode Reverse Recovery Charge | $Q_{rr}$ | | | 13 | 26 | nC |
| Reverse Recovery Fall Time | $t_a$ | | | 10 | | ns |
| Reverse Recovery Rise Time | $t_b$ | | | 15 | | |

Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

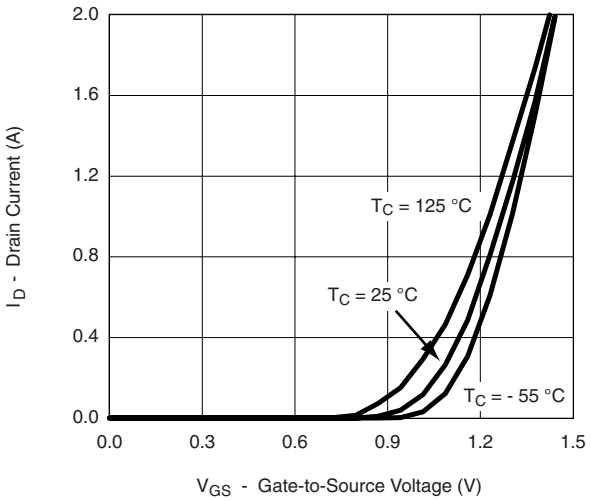
| **SCHOTTKY SPECIFICATIONS** $T_J$ = 25 °C, unless otherwise noted | | | | | | |
|---|---|---|---|---|---|---|
| **Parameter** | **Symbol** | **Test Conditions** | **Min.** | **Typ.** | **Max.** | **Unit** |
| Forward Voltage Drop | $V_F$ | $I_F$ = 0.5 A | | 0.381 | 0.46 | V |
| | | $I_F$ = 1 A | | 0.468 | 0.560 | |
| | | $I_F$ = 1 A, $T_J$ = 125 °C | | 0.44 | 0.53 | |
| Maximum Reverse Leakage Current | $I_{rm}$ | $V_r$ = 5 V | | 0.0081 | 0.041 | mA |
| | | $V_r$ = 5 V, $T_J$ = 85 °C | | 0.4 | 4 | |
| | | $V_r$ = 5 V, $T_J$ = 125 °C | | 2.8 | 28 | |
| | | $V_r$ = 10 V | | 0.0085 | 0.043 | |
| | | $V_r$ = 10 V, $T_J$ = 85 °C | | 0.5 | 5 | |
| | | $V_r$ = 10 V, $T_J$ = 125 °C | | 3 | 30 | |
| | | $V_r$ = 20 V | | 0.0093 | 0.047 | |
| | | $V_r$ = 20 V, $T_J$ = 85 °C | | 0.5 | 5 | |
| | | $V_r$ = 20 V, $T_J$ = 125 °C | | 3.2 | 32 | |
| Junction Capacitance | $C_T$ | $V_r$ = 10 V | | 30 | | pF |

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

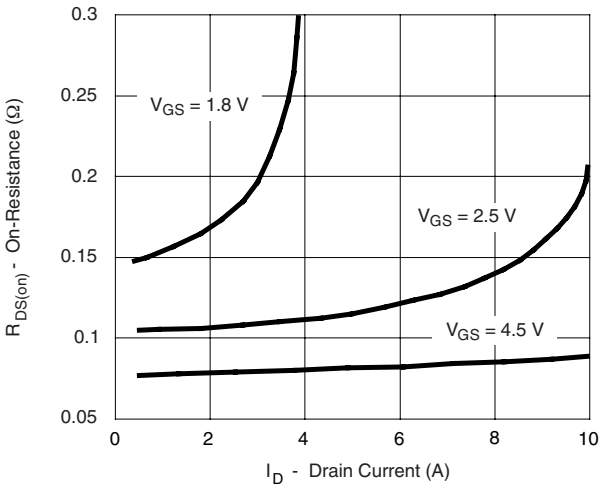
## MOSFET TYPICAL CHARACTERISTICS $T_A$ = 25 °C, unless otherwise noted



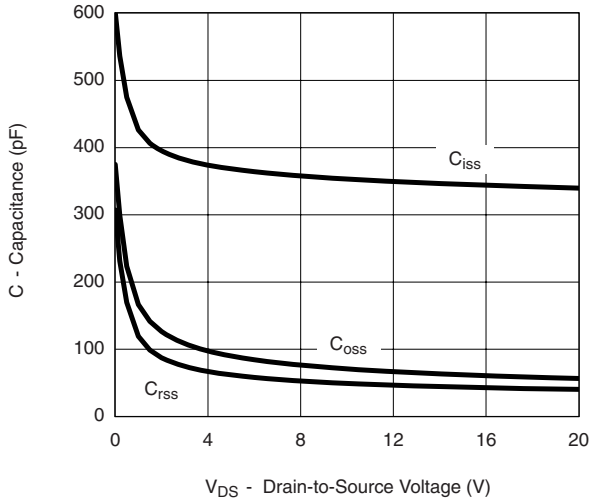

**Output Characteristics**



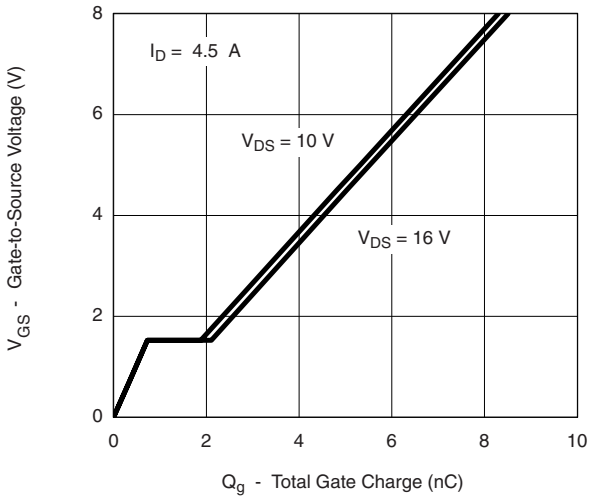

**Transfer Characteristics**



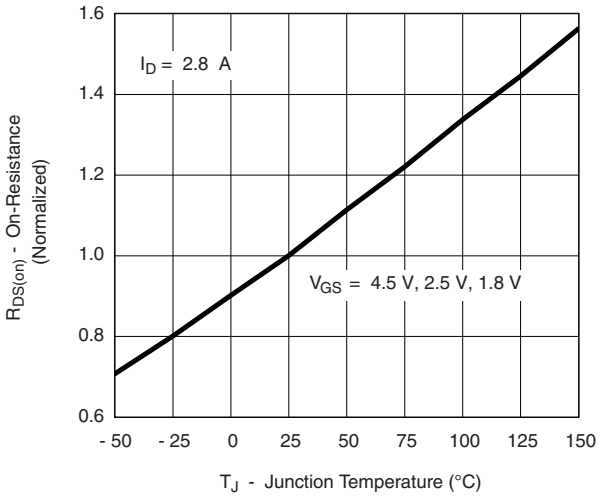

**On-Resistance vs. Drain Current and Gate Voltage**




**Capacitance**

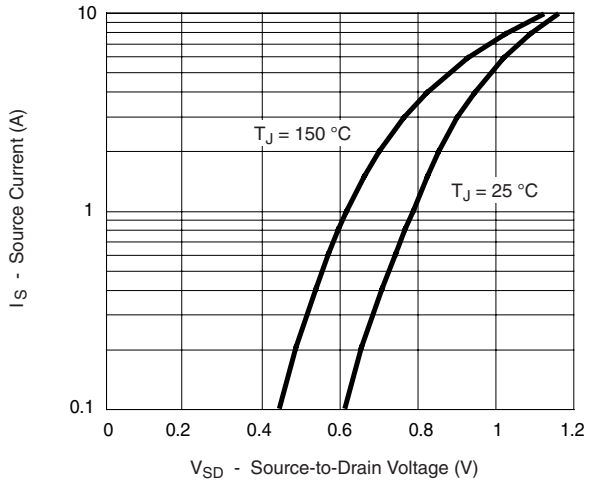



**Gate Charge**

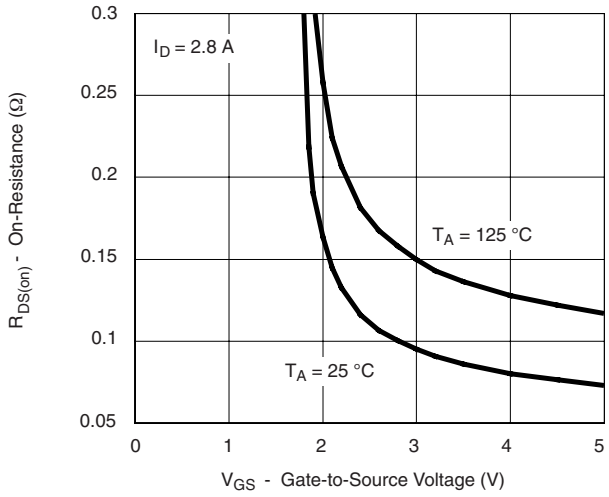



**On-Resistance vs. Junction Temperature**

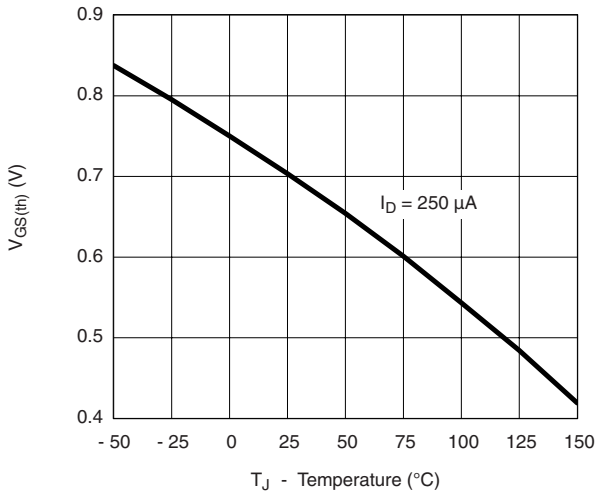
## MOSFET TYPICAL CHARACTERISTICS $T_A$ = 25 °C, unless otherwise noted



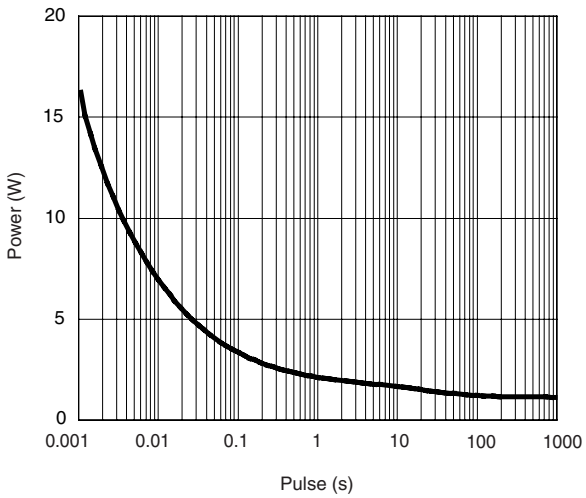

**Soure-Drain Diode Forward Voltage**



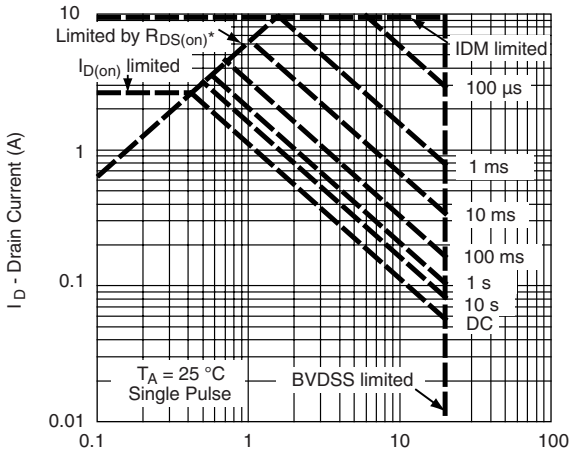

**On-Resistance vs. Gate-to-Source Voltage**




**Threshold Voltage**



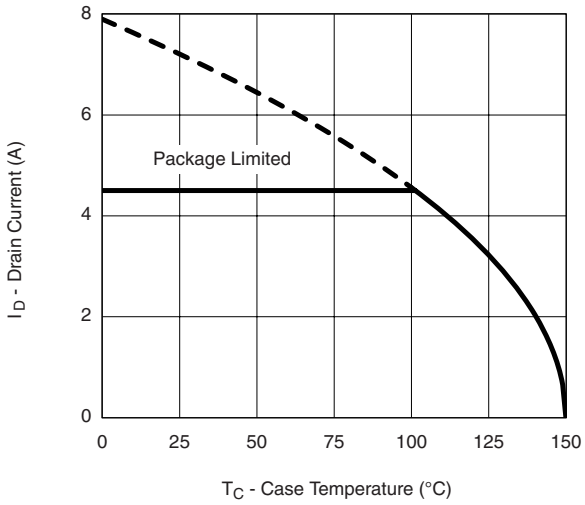

**Single Pulse Power, Junction-to-Ambient**



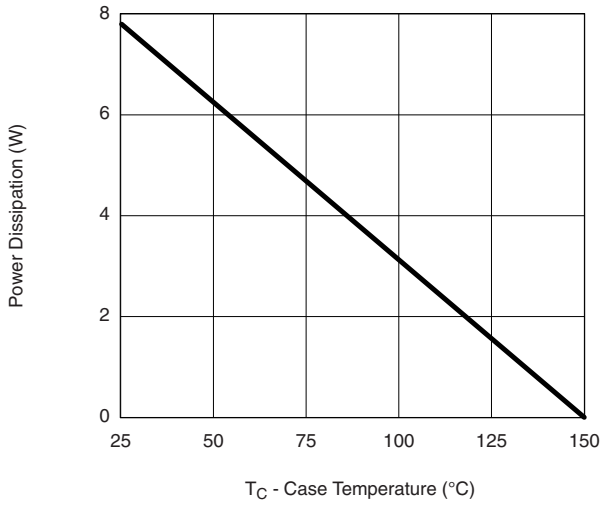

* $V_{GS}$ > minimum $V_{GS}$ at which $R_{DS(on)}$ is specified

**Safe Operating Area, Junction-to-Case**

## MOSFET TYPICAL CHARACTERISTICS $T_A$ = 25 °C, unless otherwise noted



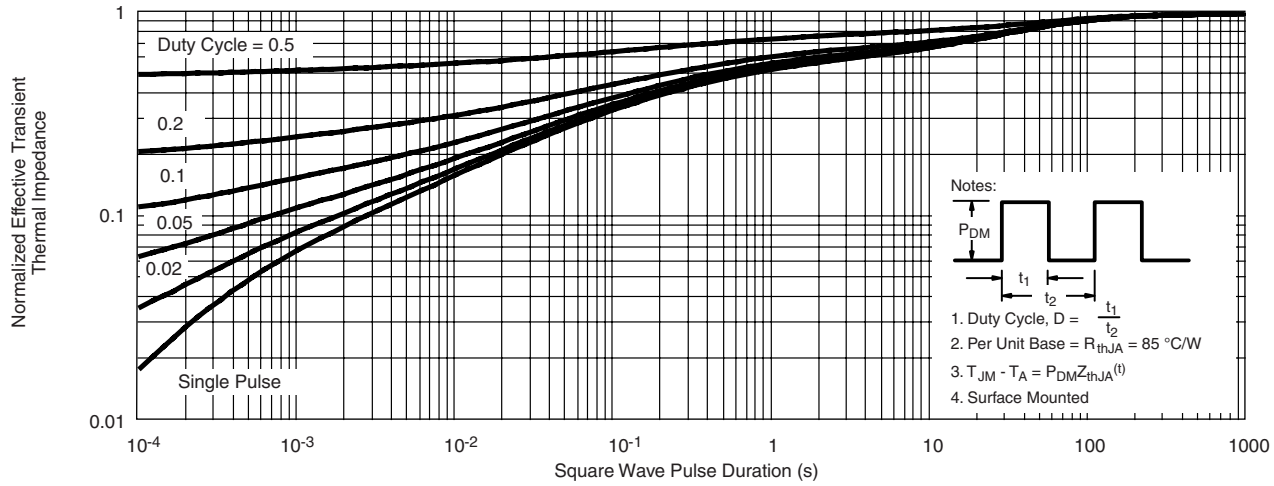

**Current Derating***



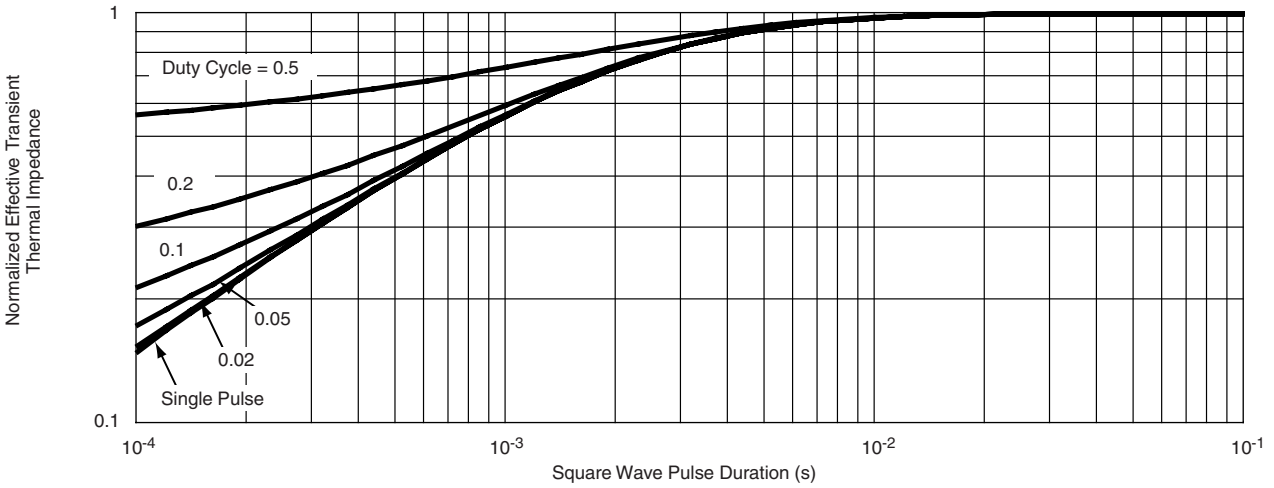

**Power Derating**

* The power dissipation $P_D$ is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

## MOSFET TYPICAL CHARACTERISTICS $T_A$ = 25 °C, unless otherwise noted

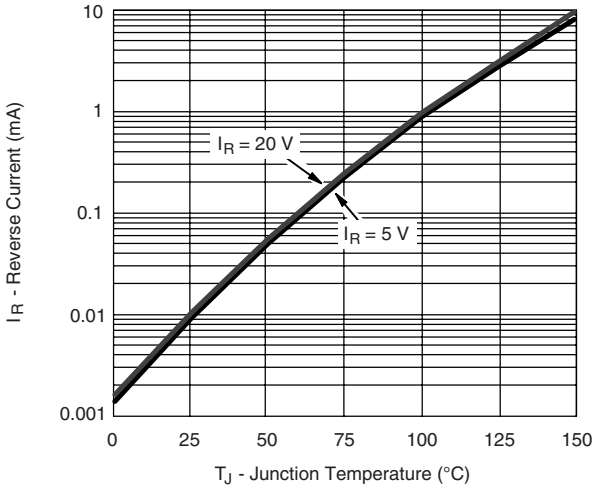



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

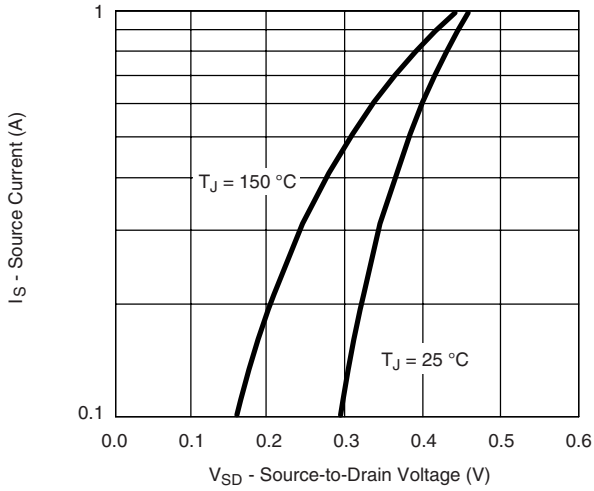



**Normalized Thermal Transient Impedance, Junction-to-Case**

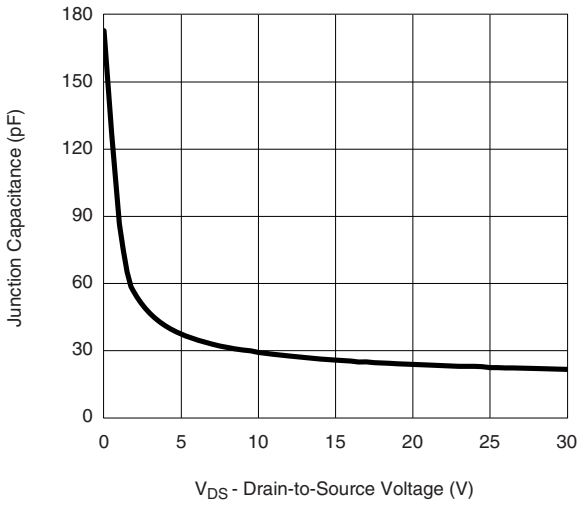
## SCHOTTKY TYPICAL CHARACTERISTICS $T_A$ = 25 °C, unless otherwise noted




**Reverse Current vs. Junction Temperature**

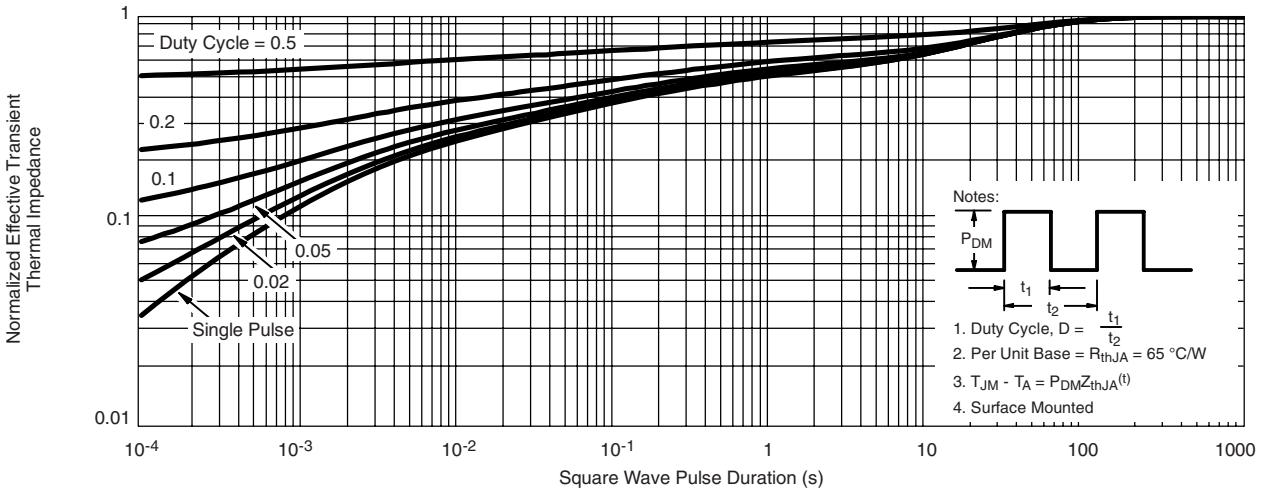



**Forward Voltage Drop**

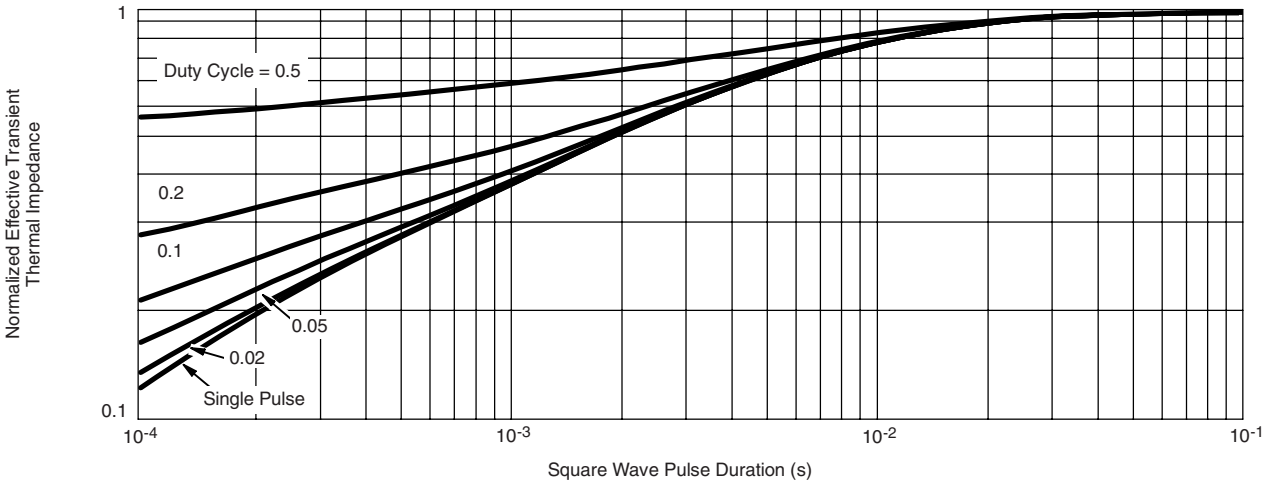



**Capacitance**

## SCHOTTKY TYPICAL CHARACTERISTICS $T_A$ = 25 °C, unless otherwise noted




**Normalized Thermal Transient Impedance, Junction-to-Ambient**




**Normalized Thermal Transient Impedance, Junction-to-Case**

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